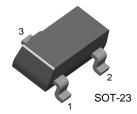


### KST4401

### **Switching Transistor**



## **NPN Epitaxial Silicon Transistor**

#### 1. Base 2. Emitter 3. Collector

### **Absolute Maximum Ratings** T<sub>a</sub>=25°C unless otherwise noted

Symbol	Parameter	Value	Units
$V_{CBO}$	Collector-Base Voltage	60	V
V <sub>CEO</sub>	Collector-Emitter Voltage	40	V
V <sub>EBO</sub>	Emitter-Base Voltage	6	V
I <sub>C</sub>	Collector Current	600	mA
P <sub>C</sub>	Collector Dissipation	350	mW
T <sub>STG</sub>	Storage Temperature	150	°C

### $\textbf{Electrical Characteristics} \ \, \textbf{T}_{a} \!\!=\!\! 25^{\circ} \textbf{C} \ \, \text{unless otherwise noted}$

Symbol	Parameter	Test Condition	Min.	Max.	Units
BV <sub>CBO</sub>	Collector-Base Breakdown Voltage	I <sub>C</sub> =100μA, I <sub>E</sub> =0	60		V
BV <sub>CEO</sub>	* Collector-Emitter Breakdown Voltage	I <sub>C</sub> =1.0mA, I <sub>B</sub> =0	40		V
BV <sub>EBO</sub>	Emitter-Base Breakdown Voltage	I <sub>E</sub> =100μA, I <sub>C</sub> =0	6		V
I <sub>BEV</sub>	Base Cut-off Current	V <sub>CE</sub> =35V, V <sub>EB</sub> =0.4V		100	nA
I <sub>CEX</sub>	Collector Cut-off Current	V <sub>CE</sub> =35V, V <sub>EB</sub> =0.4V		100	nA
h <sub>FE</sub>	* DC Current Gain	$\begin{array}{c} V_{CE} = 1 \text{V, } I_{C} = 0.1 \text{mA} \\ V_{CE} = 1 \text{V, } I_{C} = 1 \text{mA} \\ V_{CE} = 1 \text{V, } I_{C} = 10 \text{mA} \\ V_{CE} = 1 \text{V, } I_{C} = 150 \text{mA} \\ V_{CE} = 2 \text{V, } I_{C} = 500 \text{mA} \end{array}$	20 40 80 100 40	300	
V <sub>CE</sub> (sat)	* Collector-Emitter Saturation Voltage	I <sub>C</sub> =150mA, I <sub>B</sub> =15mA I <sub>C</sub> =500mA, I <sub>B</sub> =50mA		0.4 0.75	V V
V <sub>BE</sub> (sat)	* Base-Emitter Saturation Voltage	I <sub>C</sub> =150mA, I <sub>B</sub> =15mA I <sub>C</sub> =500mA, I <sub>B</sub> =50mA	0.75	0.95 1.2	V V
f <sub>T</sub>	Current Gain Bandwidth Product	I <sub>C</sub> =20mA, V <sub>CE</sub> =10V f=100MHz	250		MHz
C <sub>ob</sub>	Output Capacitance	V <sub>CB</sub> =5V, I <sub>E</sub> =0, f=100KHz		6.5	pF
t <sub>ON</sub>	Turn On Time	V <sub>CC</sub> =30V, V <sub>BE</sub> =2V I <sub>C</sub> =150mA, I <sub>B1</sub> =15mA		35	ns
t <sub>OFF</sub>	Turn Off Time	V <sub>CC</sub> =30V, I <sub>C</sub> =150mA I <sub>B1</sub> =I <sub>B2</sub> =15mA		255	ns

<sup>\*</sup> Pulse Test: Pulse Width≤300μs, Duty Cycle≤2%



# **Typical Characteristics**

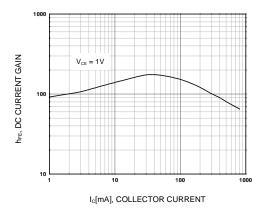


Figure 1. DC current Gain

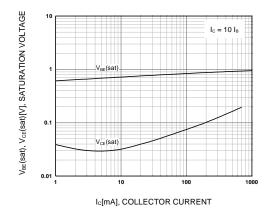


Figure 2. Collector-Emitter Saturation Voltage Base-Emitter Saturation Voltage

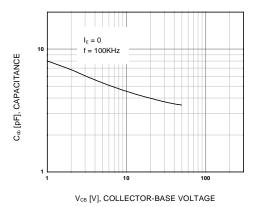


Figure 3. Collector-Base Capacitance

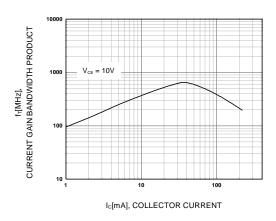
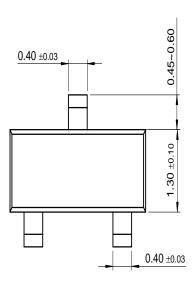
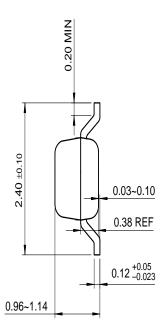


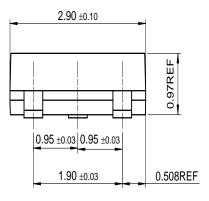
Figure 4. Current Gain Bandwidth Product

# **Package Demensions**

## **SOT-23**







Dimensions in Millimeters

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